

Docket: TSMC 98 - 262CC
S/N: 09/325,951

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A 11/2800

To:

Commissioner of Patents and Trademarks
Washington, D.C. 20231

From:

George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Serial No.: 09/325,951	Filed: 06/04/99
Inventor: Min-Hsiung Chiang	
Title: Method For Forming High Purity Silicon Oxide Field Oxide Isolation Region	
Group Art Unit: 2812	Examiner: Pompey, R. E.
Attorney Docket: TSMC 98 - 262CC	

RESPONSE TO PATENT OFFICE ACTION

Dear Sir:

In response to the Final office action dated 05/06/03, please consider the following remarks:

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450, on July 7, 2003.

Signature/Date



7/7/03

Stephen B. Ackerman

Reg. No. 37,761

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